DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1999 Apr 15 2004 Jan 13



FEATURES

- High current (max. 600 mA)
- Low voltage (max. 60 V).

APPLICATIONS

• Medium power switching.

DESCRIPTION

PNP switching transistor in a SOT23 plastic package. NPN complements: BSR13 and BSR14.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
BSR15	T7*
BSR16	T8*

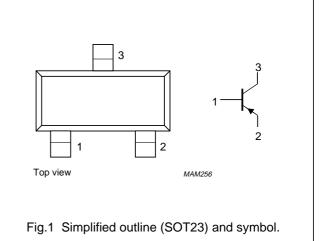
Note

- 1. * = p : Made in Hong Kong.
 - * = t : Made in Malaysia.

* = W : Made in China.

ORDERING INFORMATION

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



TYPE	PACKAGE		
NUMBER	NAME	DESCRIPTION	VERSION
BSR15	_	plastic surface mounted package; 3 leads	
BSR16			

BSR15; BSR16

BSR15; BSR16

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-60	V
V _{CEO}	collector-emitter voltage	open base			
	BSR15		_	-40	V
	BSR16		_	-60	V
V _{EBO}	emitter-base voltage	open collector	_	-5	V
I _C	collector current (DC)		_	-600	mA
I _{CM}	peak collector current		_	-800	mA
I _{BM}	peak base current		-	-200	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	_	250	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th(j-a)}	thermal resistance from junction to ambient	note 1	500	K/W

Note

1. Transistor mounted on an FR4 printed-circuit board.

BSR15; BSR16

CHARACTERISTICS

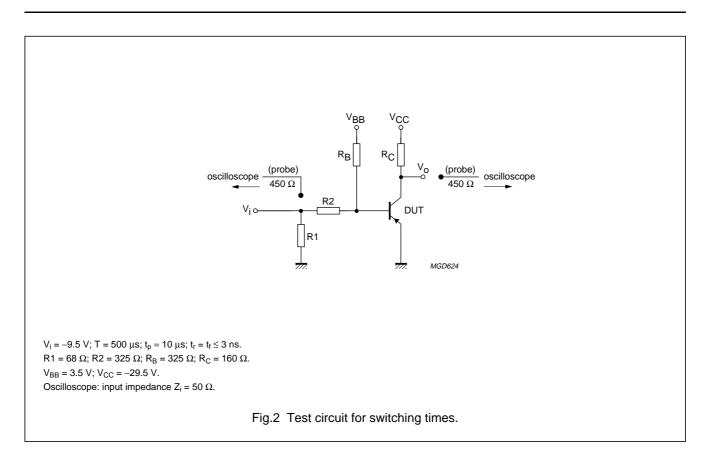
 $T_j = 25 \ ^{\circ}C$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I _{CBO}	collector cut-off current				
	BSR15	$I_E = 0; V_{CB} = -50 V$	-	-20	nA
		I _E = 0; V _{CB} = -50 V; T _j = 150 °C	-	-20	μA
	collector cut-off current				
	BSR16	$I_E = 0; V_{CB} = -50 V$	-	-10	nA
		I _E = 0; V _{CB} = -50 V; T _j = 150 °C	-	-10	μA
I _{EBO}	emitter cut-off current	$I_{C} = 0; V_{EB} = -5 V$	-	-50	nA
h _{FE}	DC current gain	$I_{C} = -0.1 \text{ mA}; V_{CE} = -10 \text{ V}$			
	BSR15		35	_	
	BSR16		75	_	
	DC current gain	$I_{C} = -1 \text{ mA}; V_{CE} = -10 \text{ V}$			
	BSR15		50	_	
	BSR16		100	_	
	DC current gain	$I_{C} = -10 \text{ mA}; V_{CE} = -10 \text{ V}$			
	BSR15		75	_	
	BSR16		100	_	
	DC current gain	$I_{C} = -150 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note } 1$	100	300	
	DC current gain	$I_{C} = -500 \text{ mA}; V_{CE} = -10 \text{ V}; \text{ note } 1$			
	BSR15		30	_	
	BSR16		50	_	
V _{CEsat}	collector-emitter saturation voltage	$I_{\rm C} = -150 \text{ mA}; I_{\rm B} = -15 \text{ mA}$	-	-400	mV
		$I_{\rm C} = -500 \text{ mA}; I_{\rm B} = -50 \text{ mA}$	_	-1.6	V
V _{BEsat}	base-emitter saturation voltage	I _C = -150 mA; I _B = -15 mA	-	-1.3	V
		$I_{\rm C} = -500 \text{ mA}; I_{\rm B} = -50 \text{ mA}$	-	-2.6	V
C _c	collector capacitance	$I_E = i_e = 0; V_{CB} = -10 V; f = 1 MHz$	-	8	pF
C _e	emitter capacitance	$I_{C} = i_{c} = 0; V_{EB} = -2 V; f = 1 MHz$	-	30	pF
f _T	transition frequency	$I_{C} = -50 \text{ mA}; V_{CE} = -20 \text{ V}; \text{ f} = 100 \text{ MHz}$	200	-	MHz
Switching t	imes (between 10% and 90% leve	els); (see Fig.2)			
t _{on}	turn-on time	$I_{Con} = -150 \text{ mA}; I_{Bon} = -15 \text{ mA};$	_	40	ns
t _d	delay time	I _{Boff} = 15 mA	-	12	ns
t _r	rise time	1	-	30	ns
t _{off}	turn-off time	1	-	365	ns
t _s	storage time	1	-	300	ns
t _f	fall time	1	-	65	ns
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Note

1. Pulse test: $t_p \leq 300 \ \mu s; \ \delta \leq 0.02.$

BSR15; BSR16

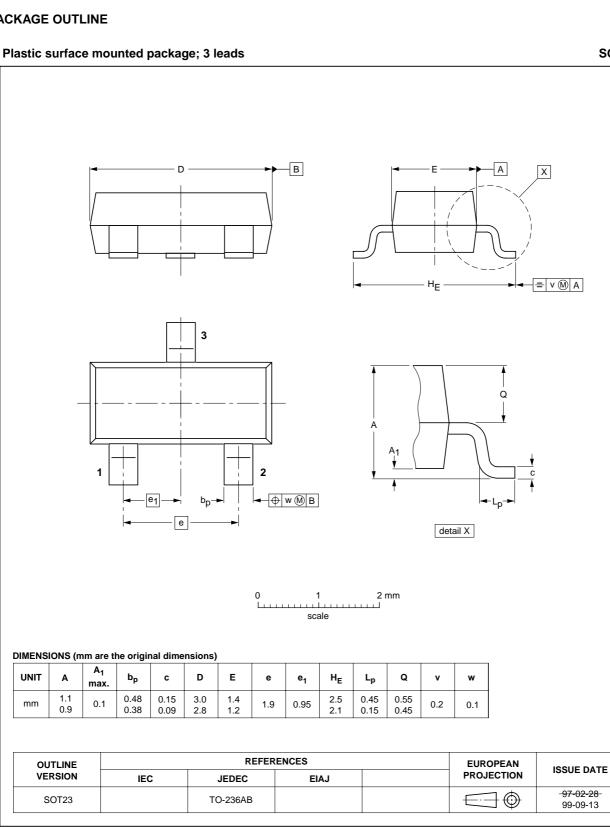


SOT23

PNP switching transistors

BSR15; BSR16

PACKAGE OUTLINE



BSR15; BSR16

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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